

## S-Band Radar Miniature Power Amplifier

Part number MPAL3035M15 is a miniaturized power amplifier which is internally matched to 50 ohms. It is designed for S-Band radar systems and operates over the instantaneous bandwidth of 3.0-3.5 GHz. It utilizes gold metal LDMOS transistor technology operating in common source configuration. Production RF performance screening is performed at the 100% level while operating under class AB bias ( $I_{DQ} = 10\text{mA}$ ) with a 300us pulse width at 10% duty. The device is operable under a wide range of biasing and pulsing conditions.



### 50 Ohm Matched

- Requires no external impedance matching circuitry

### Silicon LDMOS Transistor

- Gold Metal

### Class AB Operation

- Operable under a wide range of bias conditions

### Common Source Configuration

- Chip internal Source grounding

### Gold Metal System

- Complete Gold System Including Bond-wires
- Maximum Reliability

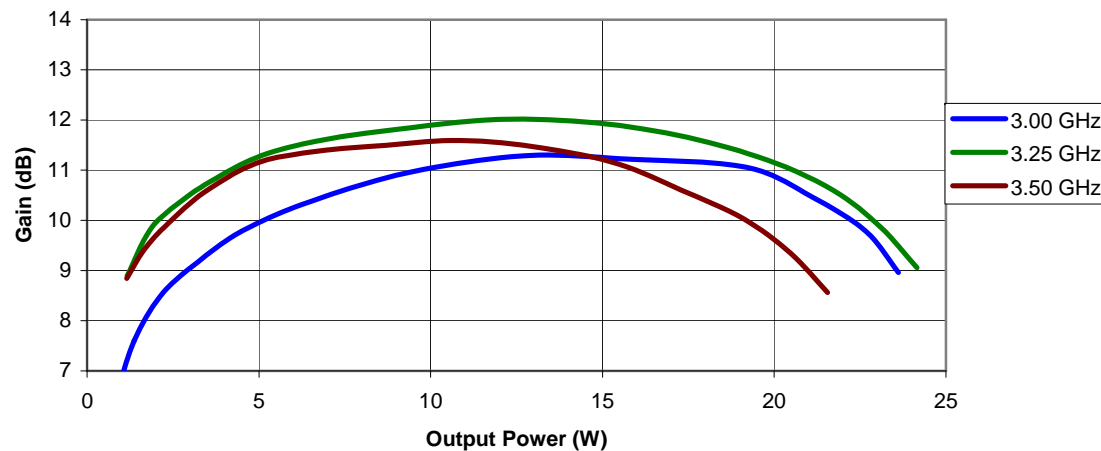
### Be0 Free Package

- Metal Based
- Epoxy seal

### RF High Power Test

- 100% Device RF High Power Screening

## TYPICAL RF GAIN VERSUS OUTPUT POWER PERFORMANCE



**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	$V_{DS}$	--	65	V	--
BD	Gate-Source Voltage	$V_{GS}$	-0.5	12	V	--
BD	Storage Temperature Range	$T_{STG}$	-55	+150	°C	--
BD	Operating Junction Temperature Range	$T_J$	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.75	°C/W	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1, P_{IN}=P_{IN1}, P_{OUT}=20W, I_D=1.6A$
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

**DC ELECTRICAL CHARACTERISTICS**

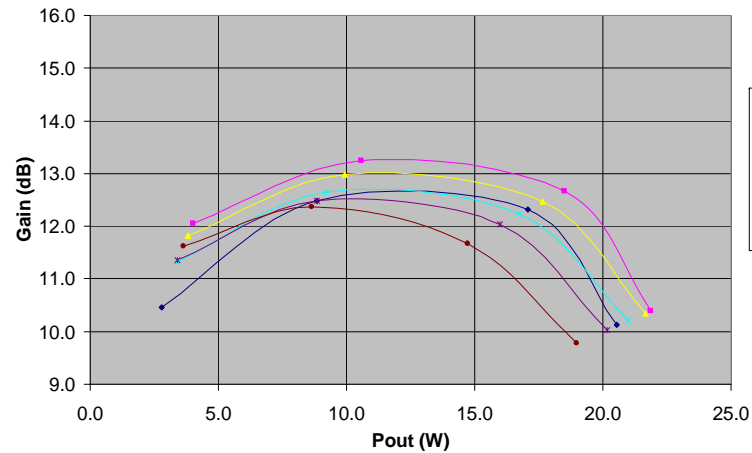
Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	$BV_{DSS}$	65	--	V	$I_{DS} = 10mA, V_{GS} = 0V, T_F = 25\pm5^\circ C.$
BD	Drain Leakage Current	$I_{DSS}$	--	1.0	$\mu A$	$V_{DS} = 32V, V_{GS} = 0V, T_F = 25\pm5^\circ C.$
100%	Operating Gate Voltage	$V_{GS}$	2.5	4.0	V	$V_{DS} = 5V, I_D = 0.1A, T_F = 25\pm5^\circ C.$
BD	Gate Leakage Current	$I_{GSS}$	--	1.0	$\mu A$	$V_{GS} = 10V, V_{DS} = 0V, T_F = 25\pm5^\circ C.$

**RF ELECTRICAL CHARACTERISTICS**

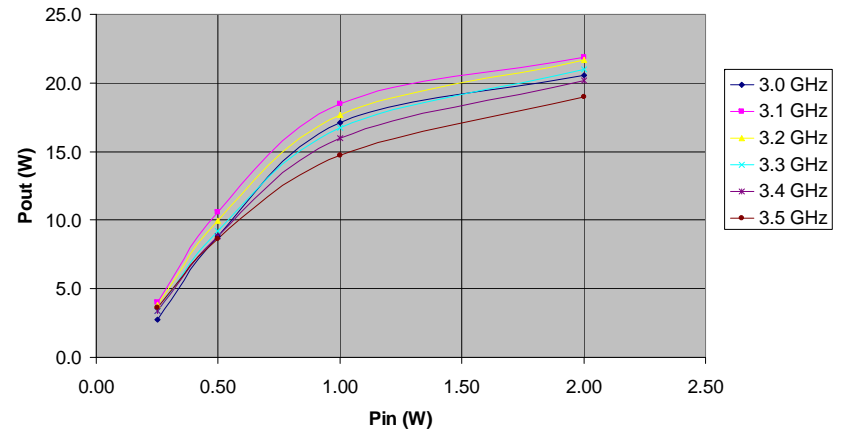
Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL1	-18	-7	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, F=F1.$
100%	Input Return Loss	IRL2	-18	-10	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN2}, F=F2.$
100%	Input Return Loss	IRL3	-18	-10	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN3}, F=F3.$
100%	Power Gain	$G_p$	11.0	15.0	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Power Gain Flatness versus Frequency	GF	0.0	1.3	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Drain Current - Peak	$I_D$	1.00	2.00	A	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Pulse Amplitude Droop	D	-0.50	+0.20	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Stability into 3:1 VSWR	VSWR-S	--	--	--	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=TF1,$ $P_{IN}= P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$ Rotate 3:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse. All non-harmonically related signals must be at least -65 dBc.
Note 1	$V1 = 32V; I_{DQ1} = 10mA; PW1 = 300\mu s; DF1 = 10\%$					
Note 2	Input Power Test Levels: $P_{IN1} = P_{IN2} = P_{IN3} = 1.0W$					
Note 3	Test Frequencies: $F1 = 3.0 GHz, F2 = 3.3 GHz, F3 = 3.5 GHz.$					
Note 4	$T_F = 25\pm 5^\circ C =$ Device Flange Temperature					

**PERFORMANCE CURVES AT  $I_{DQ}=10mA$**

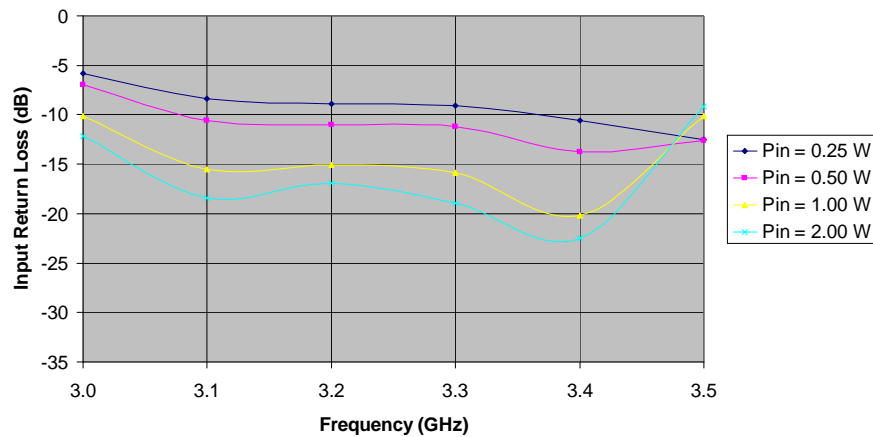
MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=10mA$



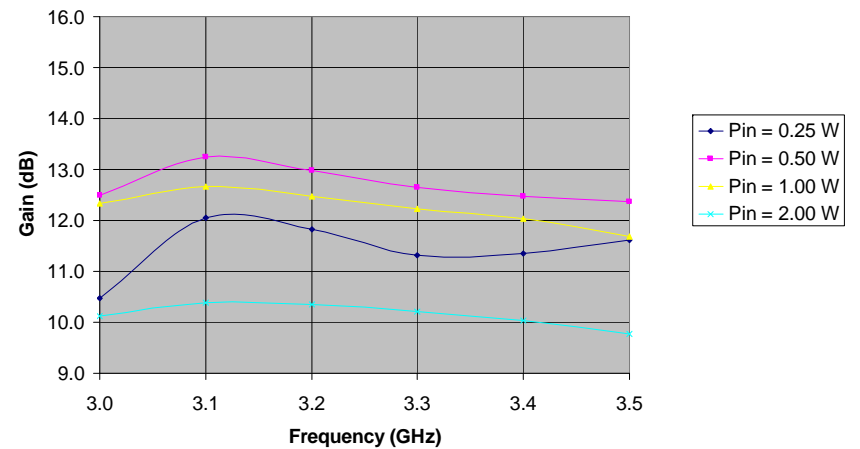
MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=10mA$



MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=10mA$

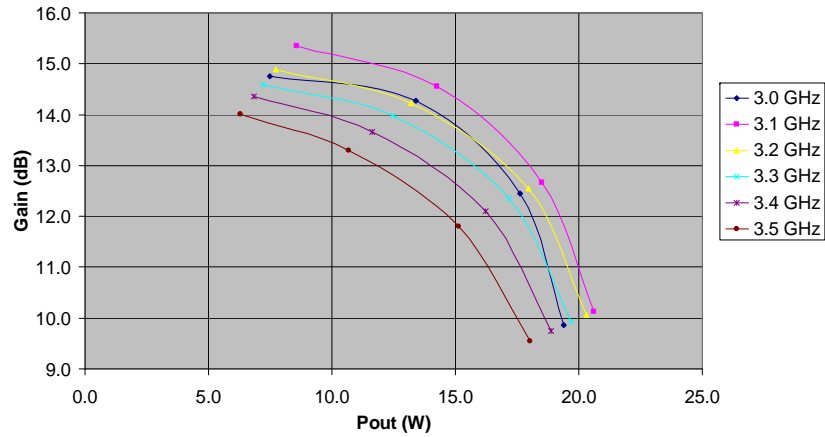


MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=10mA$

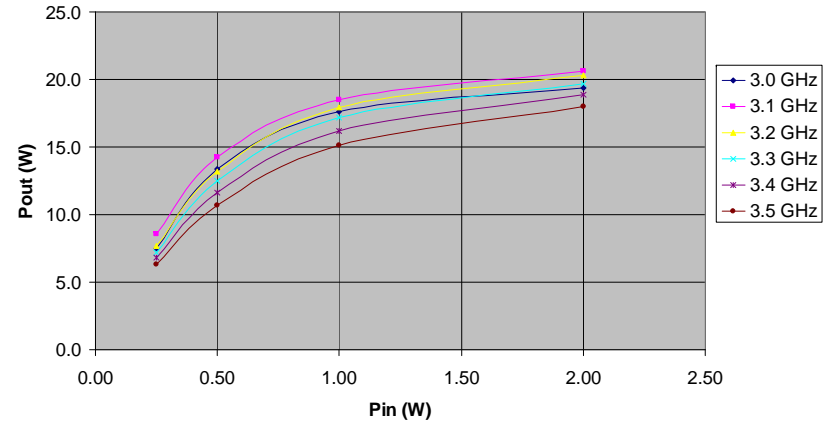


**PERFORMANCE CURVES AT  $I_{DQ}=250\text{mA}$**

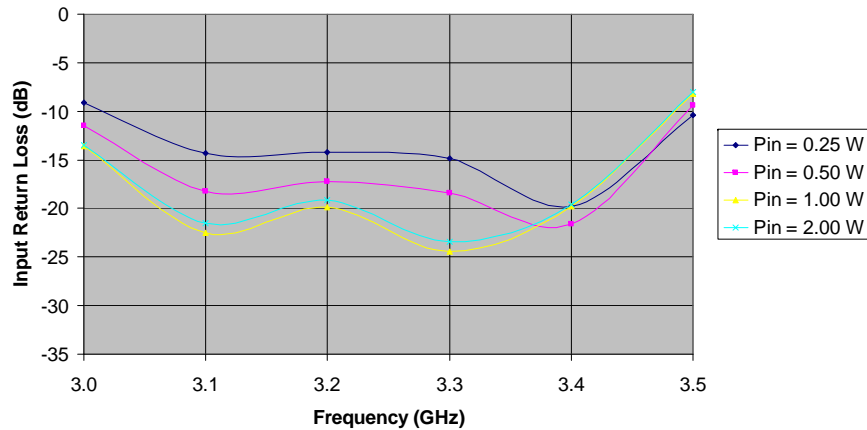
MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=250\text{mA}$



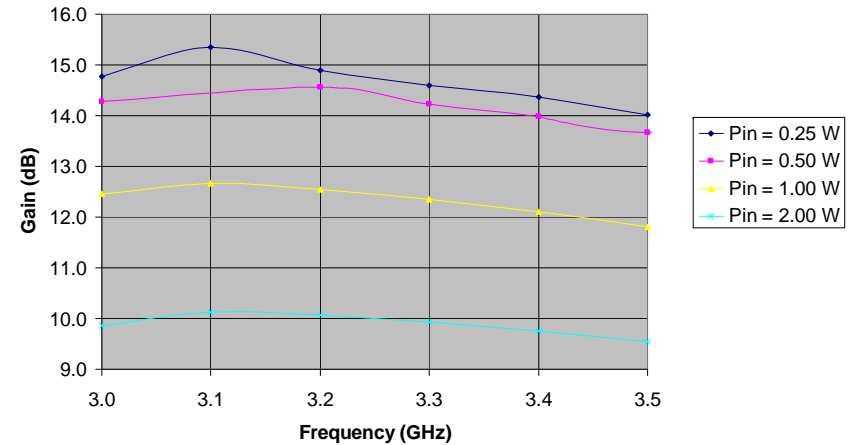
MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=250\text{mA}$



MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=250\text{mA}$

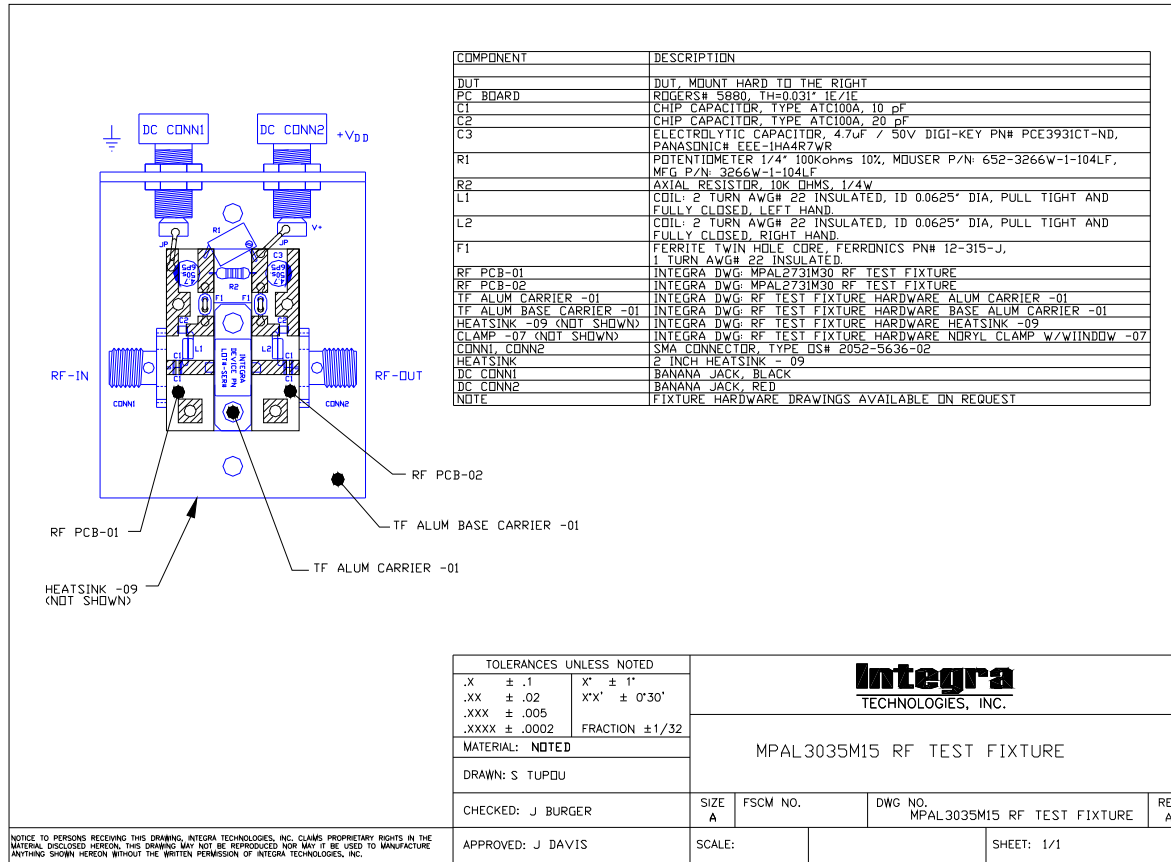


MPAL3035M15 : 100us / 10% / 28V /  $I_{DQ}=250\text{mA}$





**RF TEST FIXTURE**



**CONTACT FACTORY FOR RF TEST FIXTURE CAD DRAWING WITH CIRCUIT DIMENSIONS**

<L:\Public\Controlled Documents\Controlled Drawings\RF Test Fixture Drawings\MPAL3035M15 RF TEST FIXTURE REV A.dwg>

**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

**WARNING**

<b>Product and environmental safety - toxic materials</b>
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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